

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

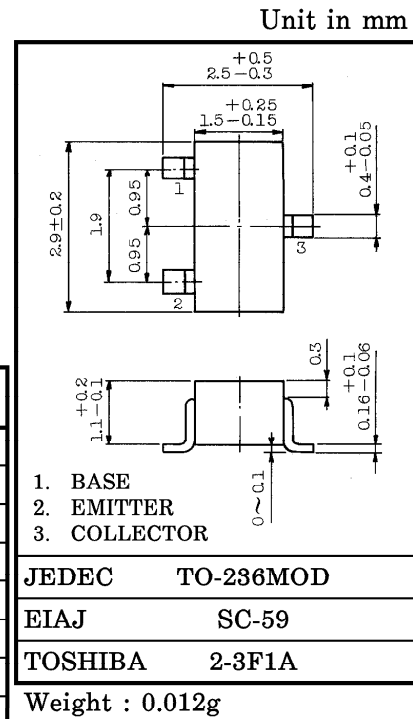
2SA1362

LOW FREQUENCY POWER AMPLIFIER APPLICATIONS.
POWER SWITCHING APPLICATIONS.

- High DC Current Gain : $h_{FE} = 120 \sim 400$
- Low Saturation Voltage
: $V_{CE(sat)} = -0.2V$ (Max.) ($I_C = -400mA, I_B = -8mA$)
- Suitable for Driver Stage of Small Motor
- Small Package

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-15	V
Collector-Emitter Voltage	V_{CEO}	-15	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Base Current	I_B	-160	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$

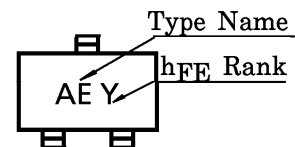


ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -15V, I_E = 0$	—	—	-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	—	—	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-15	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = -1V, I_C = -100mA$	120	—	400	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -800mA$	40	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -400mA, I_B = -8mA$	—	—	-0.2	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -1V, I_C = -10mA$	-0.5	—	-0.8	V
Transition Frequency	f_T	$V_{CE} = -5V, I_C = -10mA$	—	120	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	13	—	pF

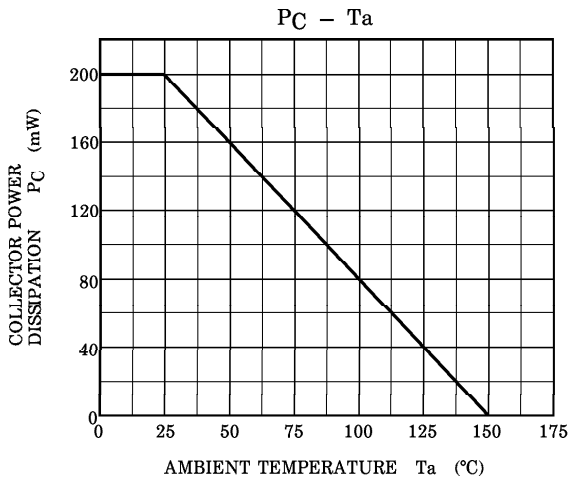
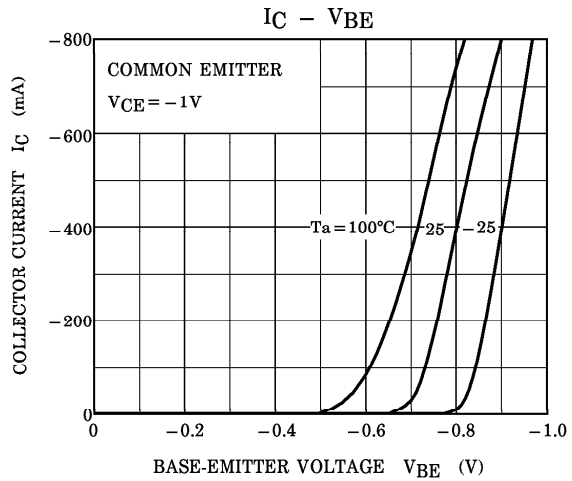
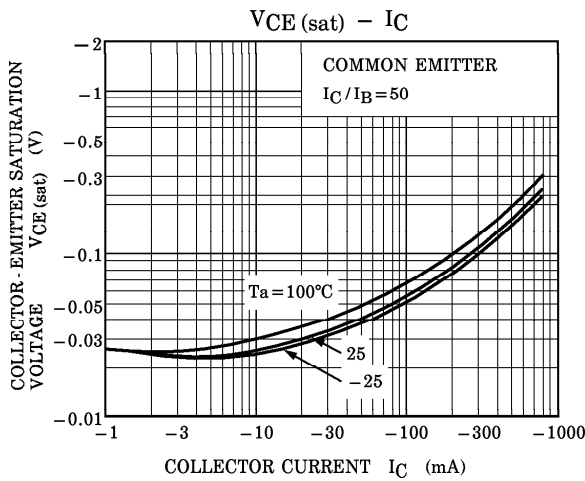
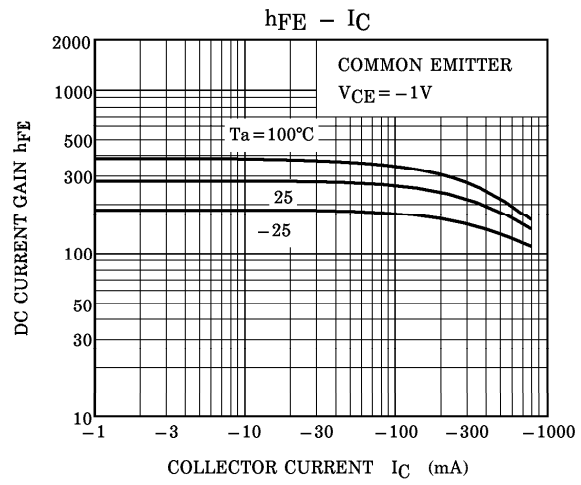
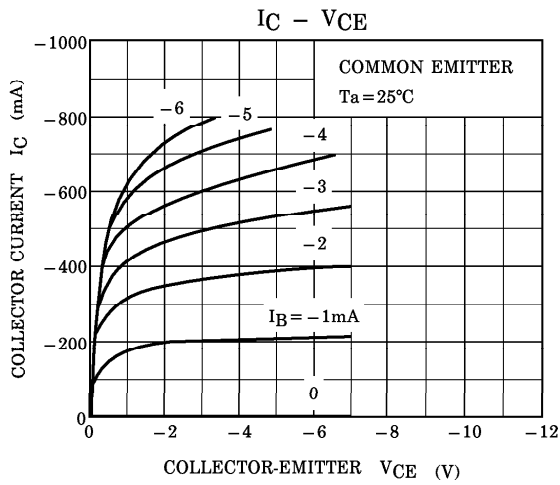
Note : $h_{FE(1)}$ Classification Y (Y) : 120~240 GR (G) : 200~400
() Marking Symbol

MARKING



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